



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

## MCH6336 — P-Channel Silicon MOSFET — General-Purpose Switching Device Applications

### Features

- Ultrahigh-speed switching
- Halogen free compliance
- 1.8V drive
- Protection diode in

### Specifications

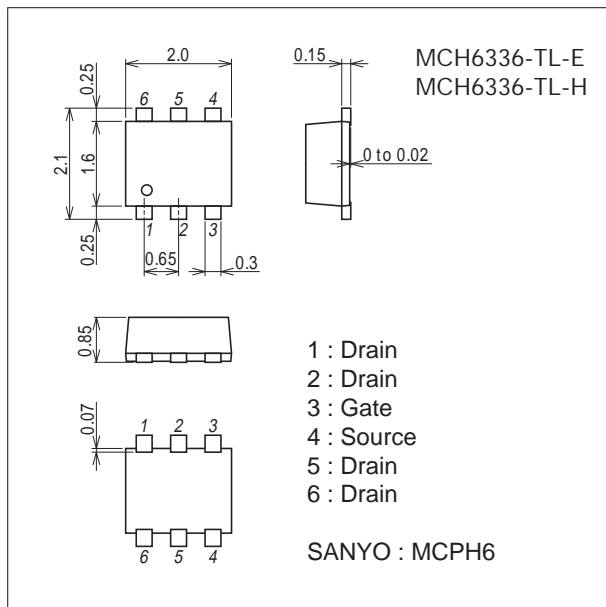
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-20	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (1200mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Package Dimensions

unit : mm (typ)

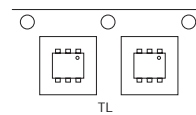
7022A-009



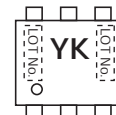
### Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

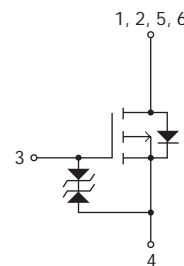
### Packing Type : TL



### Marking



### Electrical Connection

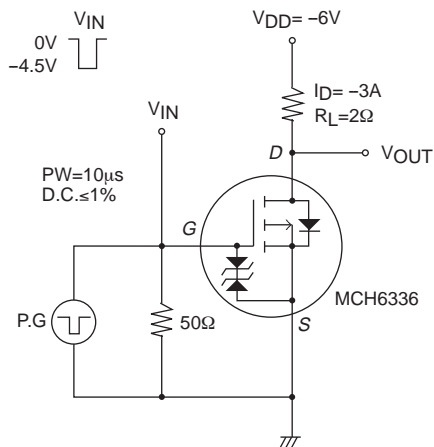


# MCH6336

## Electrical Characteristics at Ta=25°C

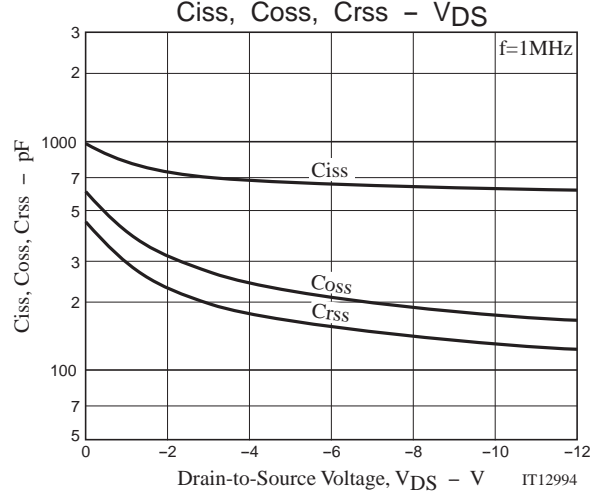
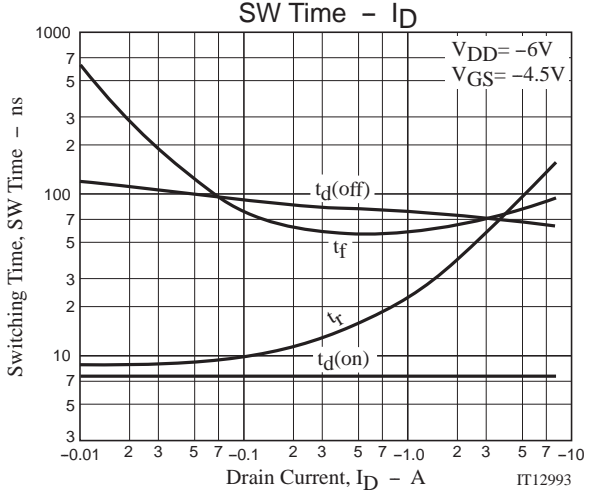
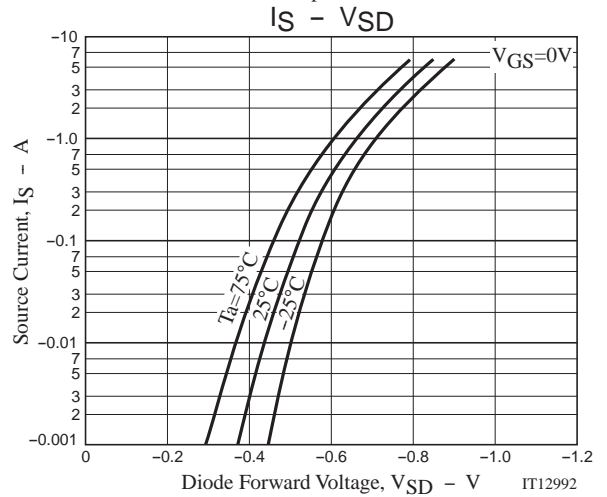
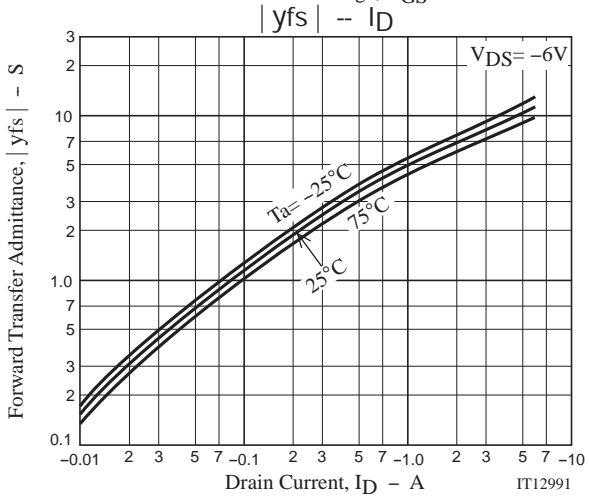
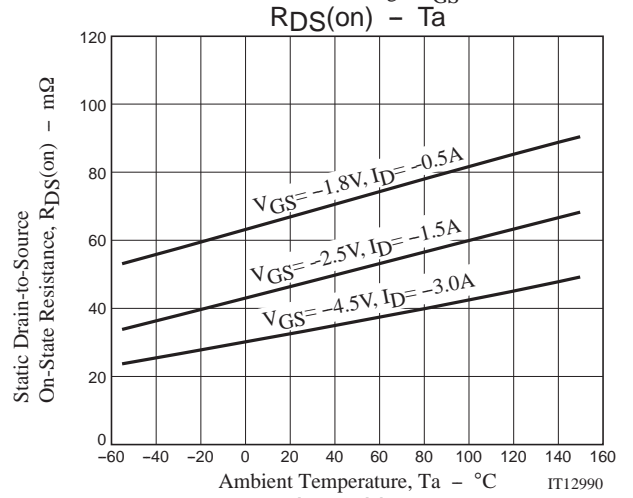
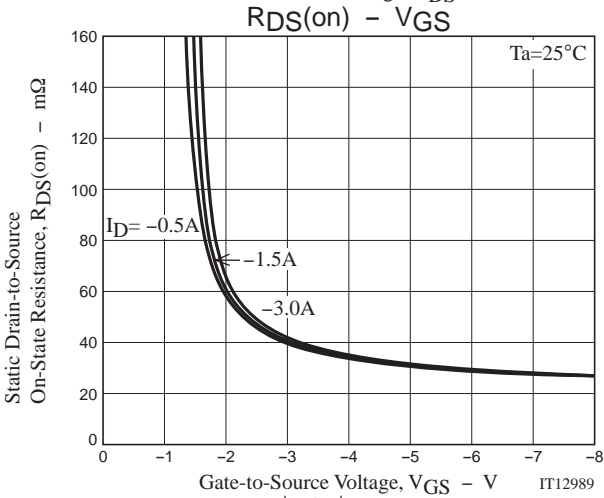
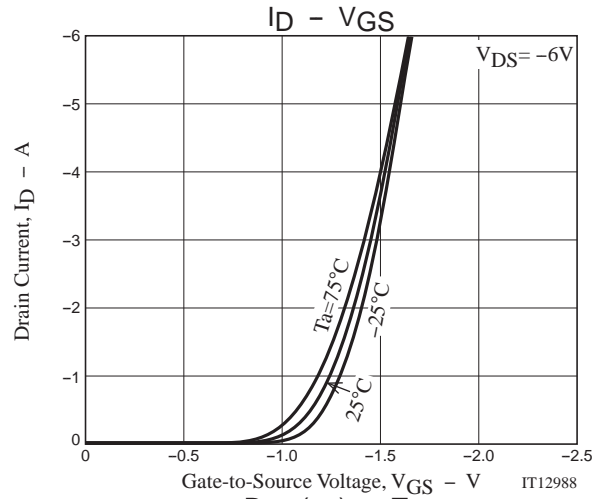
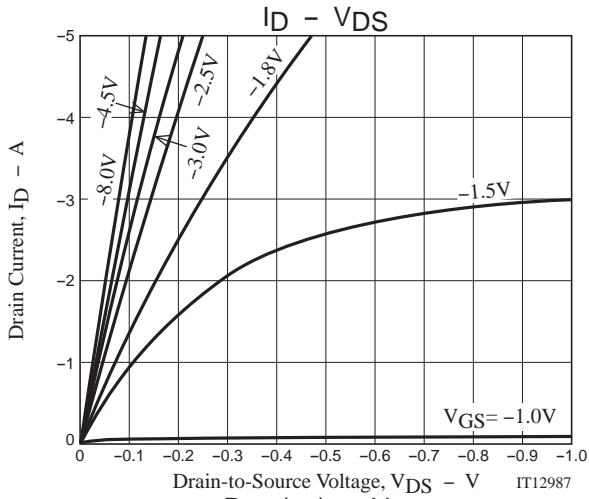
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-12V, VGS=0V			-10	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-6V, ID=-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	VDS=-6V, ID=-3A	4.8	8.1		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-3A, VGS=-4.5V		33	43	mΩ
	RDS(on)2	ID=-1.5A, VGS=-2.5V		47	66	mΩ
	RDS(on)3	ID=-0.5A, VGS=-1.8V		68	98	mΩ
Input Capacitance	Ciss	VDS=-6V, f=1MHz		660		pF
Output Capacitance	Coss			210		pF
Reverse Transfer Capacitance	Crss			155		pF
Turn-ON Delay Time	td(on)		See specified Test Circuit.		7.4	
Rise Time	tr			57		ns
Turn-OFF Delay Time	td(off)			72		ns
Fall Time	tf			69		ns
Total Gate Charge	Qg	VDS=-6V, VGS=-4.5V, ID=-5A			6.9	
Gate-to-Source Charge	Qgs			1.2		nC
Gate-to-Drain "Miller" Charge	Qgd			1.8		nC
Diode Forward Voltage	VSD	IS=-5A, VGS=0V		-0.83	-1.2	V

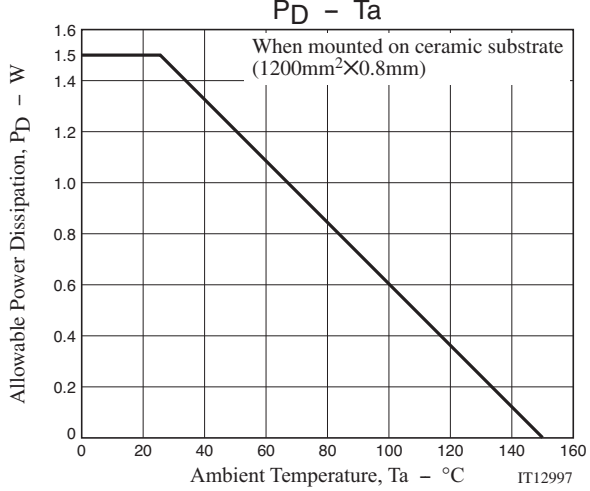
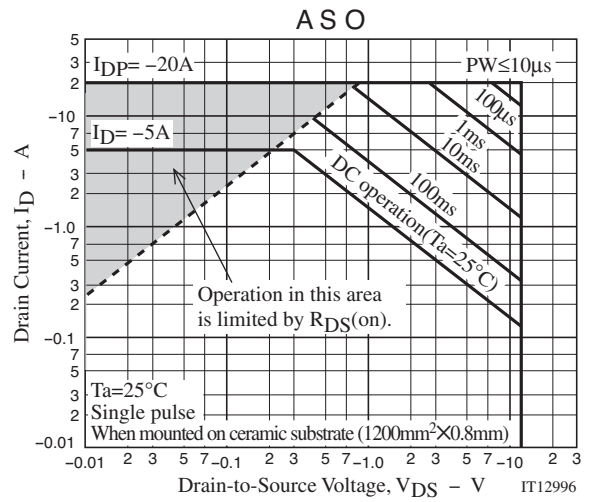
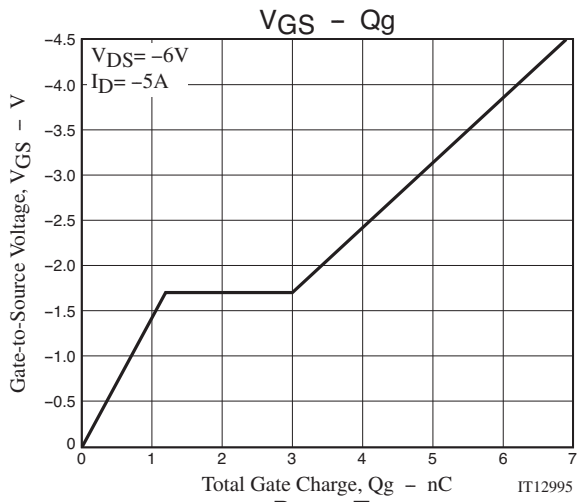
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
MCH6336-TL-E	MCPH6	3,000pcs./reel	Pb Free
MCH6336-TL-H	MCPH6	3,000pcs./reel	Pb Free and Halogen Free





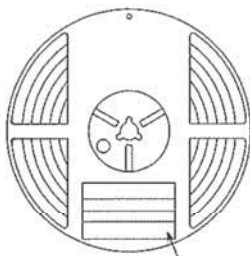
Taping Specification

MCH6336-TL-E, MCH6336-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

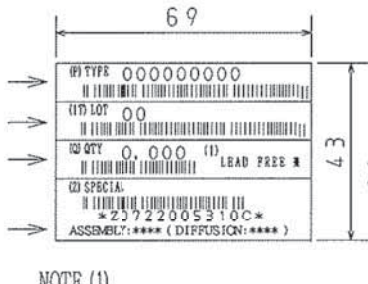
Packing method



Type No.  
LOT No.  
Quantity  
Origin

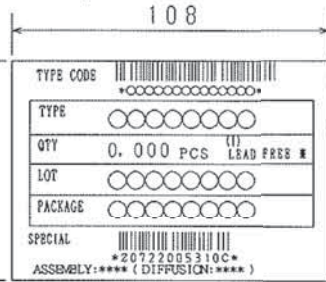
Reel label

Reel label, Inner box label  
(unit:mm)



Outer box label

(It is a label at the time of factory shipments. The form of a label may change in physical distribution process.)



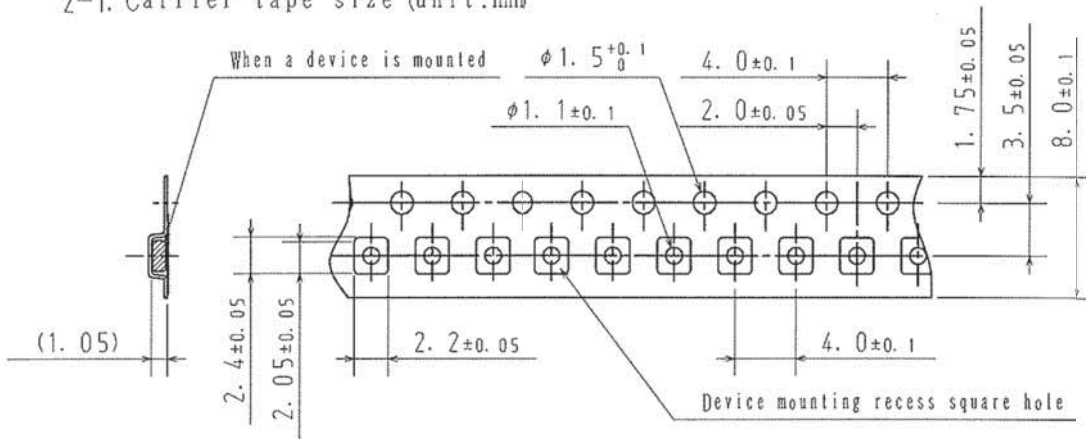
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

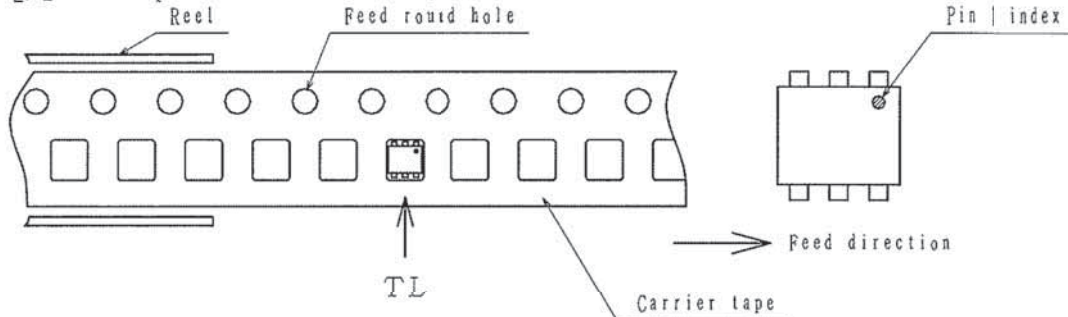
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

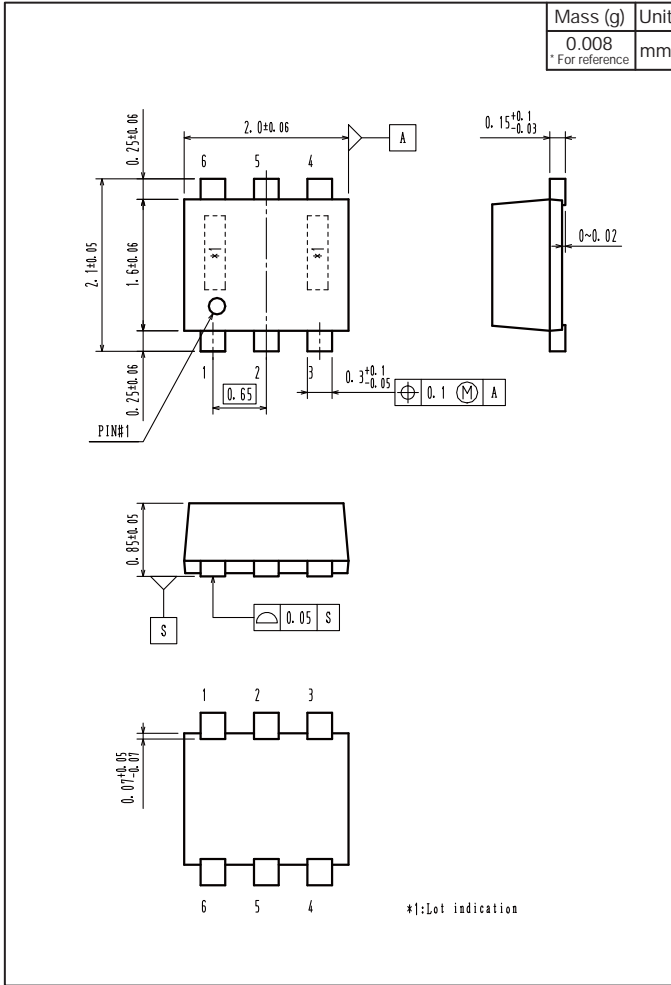


Those with pin | index on the feed hole side.....TL

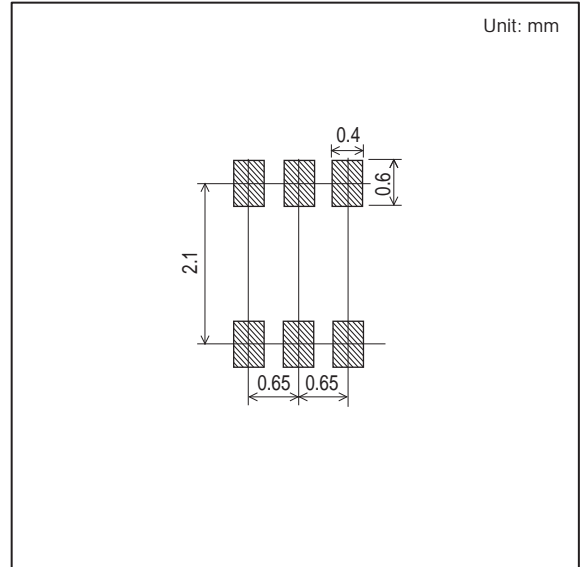
# MCH6336

## Outline Drawing

MCH6336-TL-E, MCH6336-TL-H



## Land Pattern Example



Note on usage : Since the MCH6336 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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